## Giovanni Antonio Salvatore

List of Publications by Year in descending order

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75 papers

3,989 citations

230014 27 h-index 299063 42 g-index

77 all docs

77
docs citations

times ranked

77

7515 citing authors

#	Article	IF	CITATIONS
1	Self-Sustainable Smart Ring for Long-Term Monitoring of Blood Oxygenation. IEEE Access, 2019, 7, 115400-115408.	2.6	26
2	Flexible and Lightweight Devices for Wireless Multi-Color Optogenetic Experiments Controllable via Commercial Cell Phones. Frontiers in Neuroscience, 2019, 13, 819.	1.4	17
3	Flexible Green Perovskite Light Emitting Diodes. IEEE Journal of the Electron Devices Society, 2019, 7, 769-775.	1.2	6
4	Photo-Induced Room-Temperature Gas Sensing with a-IGZO Based Thin-Film Transistors Fabricated on Flexible Plastic Foil. Sensors, 2018, 18, 358.	2.1	55
5	Charge Trapping Mechanism Leading to Sub-60-mV/decade-Swing FETs. IEEE Transactions on Electron Devices, 2017, 64, 2789-2796.	1.6	29
6	Ferroelectricâ€Like Charge Trapping Thinâ€Film Transistors and Their Evaluation as Memories and Synaptic Devices. Advanced Electronic Materials, 2017, 3, 1700309.	2.6	33
7	Lab-on-Skin: A Review of Flexible and Stretchable Electronics for Wearable Health Monitoring. ACS Nano, 2017, 11, 9614-9635.	7.3	1,245
8	Biodegradable and Highly Deformable Temperature Sensors for the Internet of Things. Advanced Functional Materials, 2017, 27, 1702390.	7.8	178
9	Buckled Thin-Film Transistors and Circuits on Soft Elastomers for Stretchable Electronics. ACS Applied Materials & Samp; Interfaces, 2017, 9, 28750-28757.	4.0	54
10	Program FFlexCom â€" High frequency flexible bendable electronics for wireless communication systems. , 2017, , .		12
11	Oxide Thin-Film Transistors on Fibers for Smart Textiles. Technologies, 2017, 5, 31.	3.0	14
11		3.0	14
	Oxide Thin-Film Transistors on Fibers for Smart Textiles. Technologies, 2017, 5, 31.  Flexible In–Ga–Zn–O-Based Circuits With Two and Three Metal Layers: Simulation and Fabrication		
12	Oxide Thin-Film Transistors on Fibers for Smart Textiles. Technologies, 2017, 5, 31.  Flexible In–Ga–Zn–O-Based Circuits With Two and Three Metal Layers: Simulation and Fabrication Study. IEEE Electron Device Letters, 2016, 37, 1582-1585.  Positive charge trapping phenomenon in n-channel thin-film transistors with amorphous alumina gate	2.2	15
12	Oxide Thin-Film Transistors on Fibers for Smart Textiles. Technologies, 2017, 5, 31.  Flexible In–Ga–Zn–O-Based Circuits With Two and Three Metal Layers: Simulation and Fabrication Study. IEEE Electron Device Letters, 2016, 37, 1582-1585.  Positive charge trapping phenomenon in n-channel thin-film transistors with amorphous alumina gate insulators. Journal of Applied Physics, 2016, 120, .  Flexible aâ€IGZO Phototransistor for Instantaneous and Cumulative UVâ€Exposure Monitoring for Skin	2.2	15 23
12 13 14	Oxide Thin-Film Transistors on Fibers for Smart Textiles. Technologies, 2017, 5, 31.  Flexible In–Ga–Zn–O-Based Circuits With Two and Three Metal Layers: Simulation and Fabrication Study. IEEE Electron Device Letters, 2016, 37, 1582-1585.  Positive charge trapping phenomenon in n-channel thin-film transistors with amorphous alumina gate insulators. Journal of Applied Physics, 2016, 120, .  Flexible aâ€IGZO Phototransistor for Instantaneous and Cumulative UVâ€Exposure Monitoring for Skin Health. Advanced Electronic Materials, 2016, 2, 1600273.	2.2	15 23 59
12 13 14	Oxide Thin-Film Transistors on Fibers for Smart Textiles. Technologies, 2017, 5, 31.  Flexible In–Ga–Zn–O-Based Circuits With Two and Three Metal Layers: Simulation and Fabrication Study. IEEE Electron Device Letters, 2016, 37, 1582-1585.  Positive charge trapping phenomenon in n-channel thin-film transistors with amorphous alumina gate insulators. Journal of Applied Physics, 2016, 120, .  Flexible aâ€IGZO Phototransistor for Instantaneous and Cumulative UVâ€Exposure Monitoring for Skin Health. Advanced Electronic Materials, 2016, 2, 1600273.  20.3dB 0.39mW AM detector with single-transistor active inductor in bendable a-IGZO TFT. , 2016, , .	2.2	15 23 59

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19	3.5 mW 1MHz AM detector and digitally-controlled tuner in a-IGZO TFT for wireless communications in a fully integrated flexible system for audio bag. , $2016$ , , .		5
20	Autonomous smartwatch with flexible sensors for accurate and continuous mapping of skin temperature. , 2016, , .		10
21	20.3dB 0.39mW AM detector with single-transistor active inductor in bendable a-IGZO TFT., 2016,,.		1
22	Design and analysis of high-gain amplifiers in flexible self-aligned a-IGZO thin-film transistor technology. Analog Integrated Circuits and Signal Processing, 2016, 87, 213-222.	0.9	9
23	Bendable energy-harvesting module with organic photovoltaic, rechargeable battery, and a-IGZO TFT charging electronics. , 2015, , .		8
24	Wireless Microfluidic Systems for Programmed, Functional Transformation of Transient Electronic Devices. Advanced Functional Materials, 2015, 25, 5100-5106.	7.8	37
25	Baseband amplifiers in a-IGZO TFT technology for flexible audio systems. , 2015, , .		2
26	20 MHz carrier frequency AM receiver in flexible a-IGZO TFT technology with textile antennas. , 2015, , .		3
27	$15~\mathrm{dB}$ Conversion gain, $20~\mathrm{MHz}$ carrier frequency AM receiver in flexible a-IGZO TFT technology with textile antennas. , $2015,$ , .		6
28	Radio frequency electronics on plastic. , 2015, , .		1
29	Stretchable and Conformable Oxide Thinâ€Film Electronics. Advanced Electronic Materials, 2015, 1, 1400038.	2.6	78
30	Flexible In–Ga–Zn–O Thin-Film Transistors on Elastomeric Substrate Bent to 2.3% Strain. IEEE Electron Device Letters, 2015, 36, 781-783.	2.2	37
31	Flexible Quasi-Vertical In-Ga-Zn-O Thin-Film Transistor With 300-nm Channel Length. IEEE Electron Device Letters, 2015, 36, 475-477.	2.2	36
32	$15\ dB$ conversion gain, 20 MHz carrier frequency AM receiver in flexible a-IGZO TFT technology with textile antennas. , 2015, , .		8
33	Cherry-Hooper amplifiers with 33 dB gain at 400 kHz BW and 10 dB gain at 3.5 MHz BW in flexible self-aligned a-IGZO TFT technology. , 2014, , .		13
34	$22.5~\mbox{dB}$ open-loop gain, $31~\mbox{kHz}$ GBW pseudo-CMOS based operational amplifier with a-IGZO TFTs on a flexible film. , $2014,$ , .		32
35	High gain amplifiers in flexible self-aligned a-IGZO thin-film-transistor technology. , 2014, , .		12
36	Contact resistance and overlapping capacitance in flexible sub-micron long oxide thin-film transistors for above 100 MHz operation. Applied Physics Letters, 2014, 105, .	1.5	57

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37	High performance flexible electronics for biomedical devices. , 2014, 2014, 4176-9.		4
38	Influence of Mechanical Bending on Flexible InGaZnO-Based Ferroelectric Memory TFTs. IEEE Transactions on Electron Devices, 2014, 61, 1085-1092.	1.6	38
39	Wafer-scale design of lightweight and transparent electronics that wraps around hairs. Nature Communications, 2014, 5, 2982.	5.8	279
40	Flexible Self-Aligned Double-Gate IGZO TFT. IEEE Electron Device Letters, 2014, 35, 69-71.	2.2	69
41	Flexible electronics based on oxide semiconductors. , 2014, , .		1
42	Fabrication and Transfer of Flexible Few-Layers MoS $<$ sub $>$ 2 $<$ /sub $>$ Thin Film Transistors to Any Arbitrary Substrate. ACS Nano, 2013, 7, 8809-8815.	7.3	185
43	Smart Textiles: From Niche to Mainstream. IEEE Pervasive Computing, 2013, 12, 81-84.	1.1	30
44	Flexible Self-Aligned Amorphous InGaZnO Thin-Film Transistors With Submicrometer Channel Length and a Transit Frequency of 135 MHz. IEEE Transactions on Electron Devices, 2013, 60, 2815-2820.	1.6	96
45	IGZO TFT-Based All-Enhancement Operational Amplifier Bent to a Radius of 5 mm. IEEE Electron Device Letters, 2013, 34, 1394-1396.	2.2	79
46	Investigation of gate material ductility enables flexible a-IGZO TFTs bendable to a radius of 1.7 mm., 2013, , .		23
47	A 2.62 MHz 762 & Description of the street o		12
48	Flexible double gate a-IGZO TFT fabricated on free standing polyimide foil. Solid-State Electronics, 2013, 84, 198-204.	0.8	49
49	Room temperature fabricated flexible NiO/IGZO pn diode under mechanical strain. Solid-State Electronics, 2013, 87, 17-20.	0.8	31
50	Textile integrated sensors and actuators for near-infrared spectroscopy. Optics Express, 2013, 21, 3213.	1.7	40
51	InGaZnO TFTs on a flexible membrane transferred to a curved surface with a radius of 2 mm., 2013,,.		5
52	A Compact a-IGZO TFT Model Based on MOSFET SPICE \${m Level}=3\$ Template for Analog/RF Circuit Designs. IEEE Electron Device Letters, 2013, 34, 1391-1393.	2.2	44
53	Mechanically flexible vertically integrated a-IGZO thin-film transistors with 500 nm channel length fabricated on free standing plastic foil. , $2013, , .$		19
54	Overview of the EC project FLEXIBILITY: Organic and thin-film ICs up to radio frequencies for multifunctional flexible systems. , $2013,  ,  .$		4

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55	Experimental confirmation of temperature dependent negative capacitance in ferroelectric field effect transistor. Applied Physics Letters, 2012, 100, .	1.5	86
56	Flexible a-IGZO TFT amplifier fabricated on a free standing polyimide foil operating at $1.2\mathrm{MHz}$ while bent to a radius of $5\mathrm{mm}$ ., $2012$ , , .		47
57	Mechanically flexible double gate a-IGZO TFTs., 2012,,.		2
58	Test structure and method for the experimental investigation of internal voltage amplification and surface potential of ferroelectric MOSFETs. Solid-State Electronics, 2011, 65-66, 151-156.	0.8	2
59	Modeling the Temperature Dependence of Fe-FET Static Characteristics Based on Landau's Theory. IEEE Transactions on Electron Devices, 2011, 58, 3162-3169.	1.6	19
60	The Hysteretic Ferroelectric Tunnel FET. IEEE Transactions on Electron Devices, 2010, 57, 3518-3524.	1.6	41
61	An experimental investigation of the surface potential in ferroelectric P(VDF-TrFE) FETs. Microelectronic Engineering, 2010, 87, 1607-1609.	1.1	5
62	(Invited) Beyond CMOS Devices as Enablers of Future Energy Efficient Integrated Circuits and Systems. ECS Transactions, 2010, 33, 73-76.	0.3	0
63	Ferroelectric Polymer Gate Transistor as a Model System for Exploring the Mechanisms of the Retention Loss. Ferroelectrics, 2010, 409, 185-189.	0.3	O
64	Test structure and method for the experimental investigation of internal voltage amplification and surface potential of ferroelectric MOSFETs. , 2010, , .		1
65	Ferroelectric transistors with improved characteristics at high temperature. Applied Physics Letters, 2010, 97, .	1.5	24
66	The Curie temperature as a key design parameter of ferroelectric Field Effect Transistors. , 2010, , .		2
67	Metal-Ferroelectric-Meta-Oxide-semiconductor field effect transistor with sub-60mV/decade subthreshold swing and internal voltage amplification. , 2010, , .		97
68	Non-hysteretic ferroelectric tunnel FET with improved conductance at Curie temperature. , 2010, , .		11
69	Retention in nonvolatile silicon transistors with an organic ferroelectric gate. Applied Physics Letters, 2009, 94, 263507.	1.5	19
70	An experimental study of temperature influence on electrical characteristics of ferroelectric P(VDF-TrFE) FETs on SOI. , 2009, , .		1
71	A study of polarization effects in Metal-Ferroelectric-Oxide-Semiconductor Capacitors. , 2009, , .		1
72	Materials and Devices for Nanoelectronic Systems Beyond Ultimately Scaled CMOS., 2009,, 23-44.		4

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73	Low voltage Ferroelectric FET with sub-100nm copolymer P(VDF-TrFE) gate dielectric for non-volatile 1T memory. , 2008, , .		9
74	Demonstration of subthrehold swing smaller than 60mV/decade in Fe-FET with P(VDF-TrFE)/SiO <inf>2</inf> gate stack. , 2008, , .		68
75	Pattern Generation by Using Multistep Room-Temperature Nanoimprint Lithography. IEEE Nanotechnology Magazine, 2007, 6, 639-644.	1.1	5